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Mark H. Somervell
Thomas I. Wallow
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- 2 Novel Processing of Patterning Materials
Dah-Chung Owe-Yang, Shin-Etsu MicroSi, Inc. (United States)
Nobuyuki N. Matsuzawa, Sony Corporation (Japan)
- 3 EUV Resists: Joint Session with Conferences 8679 and 8682
Robert L. Brainard, College of Nanoscale Science & Engineering,
University at Albany (United States)
George G. Barclay, Dow Advanced Materials (United States)
- 4 Optical Extensions
Christoph K. Hohle, Fraunhofer-Center Nanoelektronische
Technologien (Germany)
Robert Allen, IBM Almaden Research Center (United States)
- 5 Accelerated Development of Materials and Processes: Joint Session
with Conference 8681 and 8682
Clifford L. Henderson, Georgia Institute of Technology (United States)
Martha I. Sanchez, IBM Almaden Research Center (United States)
- 6 DSA Materials and Processing: Joint Session with Conference 8680
and 8682
Joy Y. Cheng, IBM Almaden Research Center (United States)
Ralph R. Dammel, AZ Electronic Materials USA Corporation (United
States)
- 7 Negative Tone Patterning
Plamen Tzviatkov, FUJIFILM Electronic Materials U.S.A., Inc.
(United States)
Scott W. Jessen, Texas Instruments Inc. (United States)
- 8 Novel Patterning Materials
Daniel P. Sanders, IBM Almaden Research Center (United States)
Ramakrishnan Ayothi, JSR Micro, Inc. (United States)
- 9 E-Beam Patterning Materials
Luisa D. Bozano, IBM Almaden Research Center (United States)
Roel Gronheid, IMEC (Belgium)

- 10 EUV Materials, Processing, and Analysis
Todd Ross Younkin, Intel Corporation (Belgium)
Roel Gronheid, IMEC (Belgium)
- 11 Fundamental Studies of RLS Behavior
Sean D. Burns, IBM Corporation (United States)
Douglas Guerrero, Brewer Science, Inc. (United States)